
2SD467

Silicon NPN Epitaxial

HITACHI

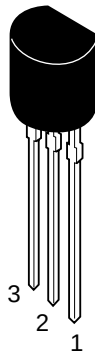
ADE-208-1134 (Z)
1st. Edition
Mar. 2001

Application

- Low frequency power amplifier
- Complementary pair with 2SB561

Outline

TO-92 (1)



1. Emitter
2. Collector
3. Base

Absolute Maximum Ratings (Ta = 25°C)

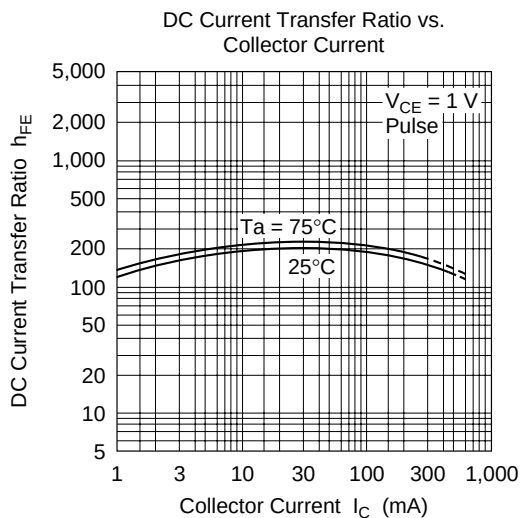
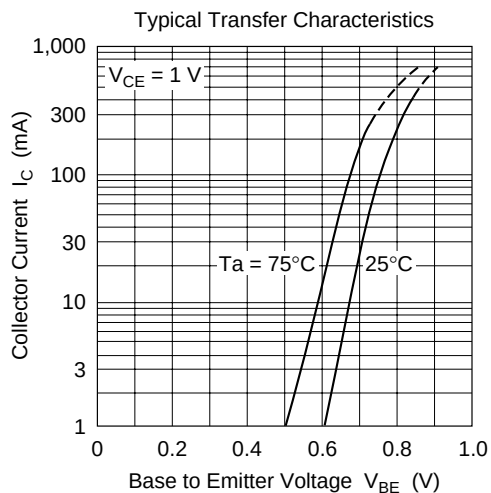
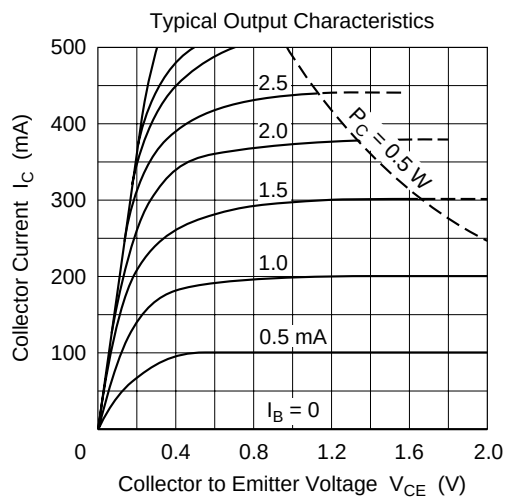
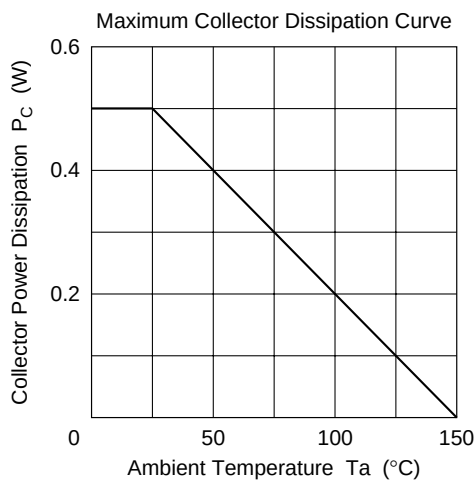
Item	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	25	V
Collector to emitter voltage	V_{CEO}	20	V
Emitter to base voltage	V_{EBO}	5	V
Collector current	I_C	0.7	A
Collector peak current	$i_{C(peak)}$	1.0	A
Collector power dissipation	P_C	0.5	W
Junction temperature	T_j	150	°C
Storage temperature	Tstg	−55 to +150	°C

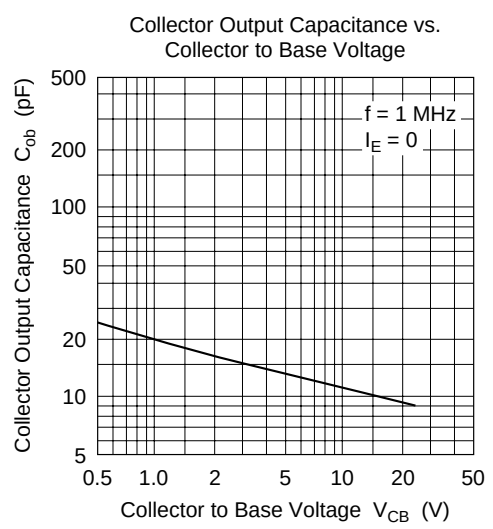
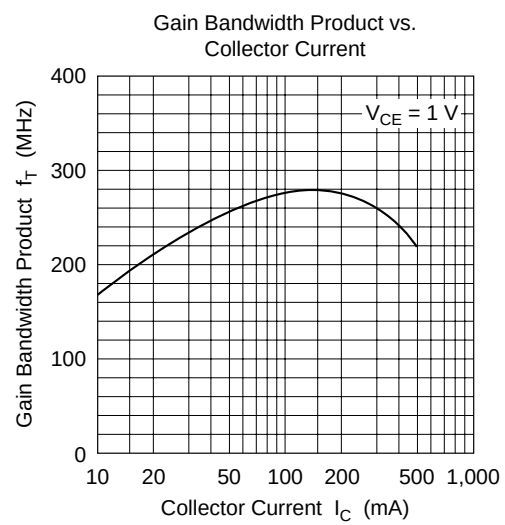
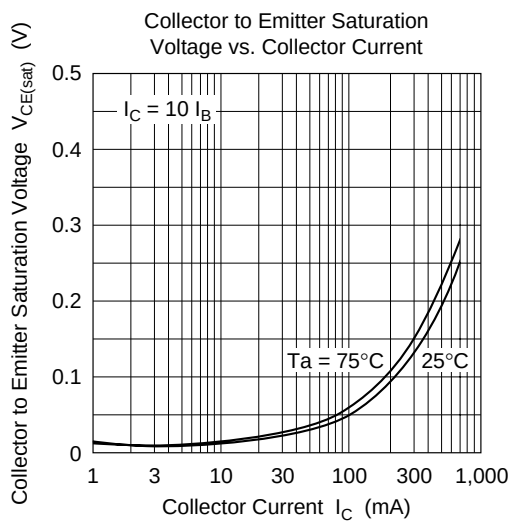
Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	25	—	—	V	$I_C = 10\text{ }\mu\text{A}$, $I_E = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	20	—	—	V	$I_C = 1\text{ mA}$, $R_{BE} = \infty$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	5	—	—	V	$I_E = 10\text{ }\mu\text{A}$, $I_C = 0$
Collector cutoff current	I_{CBO}	—	—	1.0	μA	$V_{CB} = 20\text{ V}$, $I_E = 0$
DC current transfer ratio	h_{FE}^{*1}	85	—	240		$V_{CE} = 1\text{ V}$, $I_C = 0.15\text{ A}$ (Pulse test)
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	0.19	0.5	V	$I_C = 0.5\text{ A}$, $I_B = 0.05\text{ A}$ (Pulse test)
Base to emitter voltage	V_{BE}	—	0.76	1.0	V	$V_{CE} = 1\text{ V}$, $I_C = 0.15\text{ A}$ (Pulse test)
Gain bandwidth product	f_T	—	280	—	MHz	$V_{CE} = 1\text{ V}$, $I_C = 0.15\text{ A}$ (Pulse test)
Collector output capacitance	Cob	—	12	—	pF	$V_{CB} = 10\text{ V}$, $I_E = 0$, $f = 1\text{ MHz}$

Note: 1. The 2SD467 is grouped by h_{FE} as follows.

B	C
85 to170	120 to 240

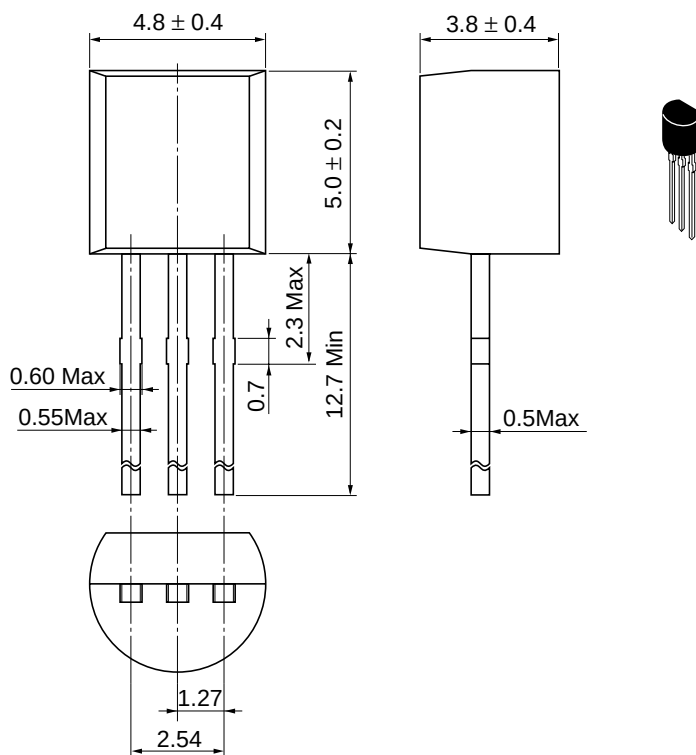




Package Dimensions

As of January, 2001

Unit: mm



Hitachi Code	TO-92 (1)
JEDEC	Conforms
EIAJ	Conforms
Mass (reference value)	0.25 g

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